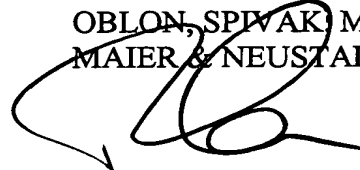


REMARKS

Applicants appreciate the indication that Claim 16 is allowable. By the above amendment, Applicant has accepted this allowable subject matter without prejudice or disclaimer. A Notice of Allowance is earnestly solicited.

Respectfully submitted,

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Amendment Filed: Herewith

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IN THE CLAIMS

- 1. (Amended) A semiconductor structure comprising:
a monocrystalline substrate;
an amorphous layer formed on the substrate; and
a first monocrystalline nitride material layer overlying the amorphous layer and
formed of at least one selected from the group [comprising] consisting of GaN, GaInN,
AlGa_{0.5}N, SiN and AlN, wherein the first monocrystalline nitride material layer is formed by
nitridation of a first monocrystalline material layer selected from the group
consisting of GaAs, GaInAs, AlGaAs, Si and AlAs, and wherein said first monocrystalline
material layer has a thickness in the range of from about 20 angstroms to about 50 angstroms.
3. (Cancelled).
16-42. (Cancelled).
43. (New).--